What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, Cap Sense, DMA, I²S, POR, PWM, WDT
Number of I/O	83
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 25x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l151vct6tr

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2 Description

The ultra-low-power STM32L151xC and STM32L152xC devices incorporate the connectivity power of the universal serial bus (USB) with the high-performance ARM® Cortex®-M3 32-bit RISC core operating at a frequency of 32 MHz (33.3 DMIPS), a memory protection unit (MPU), high-speed embedded memories (Flash memory up to 256 Kbytes and RAM up to 32 Kbytes) and an extensive range of enhanced I/Os and peripherals connected to two APB buses.

The STM32L151xC and STM32L152xC devices offer two operational amplifiers, one 12-bit ADC, two DACs, two ultra-low-power comparators, one general-purpose 32-bit timer, six general-purpose 16-bit timers and two basic timers, which can be used as time bases.

Moreover, the STM32L151xC and STM32L152xC devices contain standard and advanced communication interfaces: up to two I2Cs, three SPIs, two I2S, three USARTs and an USB. The STM32L151xC and STM32L152xC devices offer up to 23 capacitive sensing channels to simply add a touch sensing functionality to any application.

They also include a real-time clock and a set of backup registers that remain powered in Standby mode.

Finally, the integrated LCD controller (except STM32L151xC devices) has a built-in LCD voltage generator that allows to drive up to 8 multiplexed LCDs with the contrast independent of the supply voltage.

The ultra-low-power STM32L151xC and STM32L152xC devices operate from a 1.8 to 3.6 V power supply (down to 1.65 V at power down) with BOR and from a 1.65 to 3.6 V power supply without BOR option. They are available in the -40 to +85 °C and -40 to +105 °C temperature ranges. A comprehensive set of power-saving modes allows the design of low-power applications.

2.1 Device overview

Table 2. Ultra-low-power STM32L151xC and STM32L152xC device features and peripheral counts

Peripheral		STM32L15xCC	STM32L15xUC STM32L15xRC	STM32L15xVC
Flash (Kbytes)		256		
Data EEPROM (Kbytes)		8		
RAM (Kbytes)		32		
Timers	**32 bit**	1		
	General-purpose	6		
	Basic	2		
Communication interfaces	**SPI**	8(3)(1)		
	I^{2}S	2		
	I^{2}C	2		
	USART	3		
	USB	1		
GPIOs		37	51	83
Operation amplifiers		2		
12-bit synchronized ADC **Number of channels**		1 14	1 21	1 25
12-bit DAC **Number of channels**		2 2		
LCD (2) **COM x SEG**		1 4x18	1 4x32 or 8x28	1 4x44 or 8x40
Comparators		2		
Capacitive sensing channels		16	23	
Max. CPU frequency		32 MHz		
Operating voltage		1.8 V to 3.6 V (down to 1.65 V at power-down) with BOR option 1.65 V to 3.6 V without BOR option		
Operating temperatures		Ambient operating temperature: -40 °C to 85 °C / -40 °C to 105 °C Junction temperature: –40 to + 110 °C		
Packages		LQFP48, UFQFPN48	LQFP64, WLCSP63	LQFP100, UFBGA100

1. 5 SPIs are USART configured in synchronous mode emulating SPI master.
2. STM32L152xx devices only.

3.5 Low-power real-time clock and backup registers

The real-time clock (RTC) is an independent BCD timer/counter. Dedicated registers contain the sub-second, second, minute, hour (12/24 hour), week day, date, month, year, in BCD (binary-coded decimal) format. Correction for 28, 29 (leap year), 30, and 31 day of the month are made automatically. The RTC provides two programmable alarms and programmable periodic interrupts with wakeup from Stop and Standby modes.

The programmable wakeup time ranges from 120 µs to 36 hours.

The RTC can be calibrated with an external 512 Hz output, and a digital compensation circuit helps reduce drift due to crystal deviation.

The RTC can also be automatically corrected with a 50/60Hz stable powerline.

The RTC calendar can be updated on the fly down to sub second precision, which enables network system synchronization.

A time stamp can record an external event occurrence, and generates an interrupt.

There are thirty-two 32-bit backup registers provided to store 128 bytes of user application data. They are cleared in case of tamper detection.

Three pins can be used to detect tamper events. A change on one of these pins can reset backup register and generate an interrupt. To prevent false tamper event, like ESD event, these three tamper inputs can be digitally filtered.

3.6 GPIOs (general-purpose inputs/outputs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions, and can be individually remapped using dedicated AFIO registers. All GPIOs are high current capable. The alternate function configuration of I/Os can be locked if needed following a specific sequence in order to avoid spurious writing to the I/O registers. The I/O controller is connected to the AHB with a toggling speed of up to 16 MHz.

External interrupt/event controller (EXTI)

The external interrupt/event controller consists of 24 edge detector lines used to generate interrupt/event requests. Each line can be individually configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the Internal APB2 clock period. Up to 83 GPIOs can be connected to the 16 external interrupt lines. The 8 other lines are connected to RTC, PVD, USB, comparator events or capacitive sensing acquisition.

3.9 LCD (liquid crystal display)

The LCD drives up to 8 common terminals and 44 segment terminals to drive up to 320 pixels.

- Internal step-up converter to guarantee functionality and contrast control irrespective of V_{DD}. This converter can be deactivated, in which case the V_{LCD} pin is used to provide the voltage to the LCD
- Supports static, 1/2, 1/3, 1/4 and 1/8 duty
- Supports static, 1/2, 1/3 and 1/4 bias
- Phase inversion to reduce power consumption and EMI
- Up to 8 pixels can be programmed to blink
- Unneeded segments and common pins can be used as general I/O pins
- LCD RAM can be updated at any time owing to a double-buffer
- The LCD controller can operate in Stop mode
- V_{LCD} rail decoupling capability

Table 6. V_{LCD} rail decoupling

	Bias			Pin	
	1/2	1/3	1/4		
$V_{LCDRAIL1}$	1/2 V_{LCD}	2/3 V_{LCD}	1/2 V_{LCD}	PB2	
$V_{LCDRAIL2}$	N/A	1/3 V_{LCD}	1/4 V_{LCD}	PB12	PE11
$V_{LCDRAIL3}$	N/A	N/A	3/4 V_{LCD}	PB0	PE12

3.10 ADC (analog-to-digital converter)

A 12-bit analog-to-digital converters is embedded into STM32L151xC and STM32L152xC devices with up to 25 external channels, performing conversions in single-shot or scan mode. In scan mode, automatic conversion is performed on a selected group of analog inputs with up to 24 external channels in a group.

The ADC can be served by the DMA controller.

An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all scanned channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

The events generated by the general-purpose timers (TIMx) can be internally connected to the ADC start triggers, to allow the application to synchronize A/D conversions and timers. An injection mode allows high priority conversions to be done by interrupting a scan mode which runs in as a background task.

The ADC includes a specific low-power mode. The converter is able to operate at maximum speed even if the CPU is operating at a very low frequency and has an auto-shutdown function. The ADC’s runtime and analog front-end current consumption are thus minimized whatever the MCU operating mode.

Table 9. STM32L151xC and STM32L152xC pin definitions (continued)

Pins					Pin name	Pin type[1]	I / O Structure	Main function[2] (after reset)	Pin functions	
UFBGA100	LQFP100	LQFP64	WLCSP63	LQFP48 or UFQFPN48					Alternate functions	Additional functions
E11	64	38	E1	-	PC7	I/O	FT	PC7	TIM3_CH2/I2S3_MCK/ LCD_SEG25	-
E10	65	39	D1	-	PC8	I/O	FT	PC8	TIM3_CH3/LCD_SEG26	-
D12	66	40	E2	-	PC9	I/O	FT	PC9	TIM3_CH4/LCD_SEG27	-
D11	67	41	E3	29	PA8	I/O	FT	PA8	USART1_CK/MCO/ LCD_COM0	-
D10	68	42	C1	30	PA9	I/O	FT	PA9	USART1_TX/ LCD_COM1	-
C12	69	43	D2	31	PA10	I/O	FT	PA10	USART1_RX/ LCD_COM2	-
B12	70	44	B1	32	PA11	I/O	FT	PA11	USART1_CTS/ SPI1_MISO	USB_DM
A12	71	45	D3	33	PA12	I/O	FT	PA12	USART1_RTS/ SPI1_MOSI	USB_DP
A11	72	46	C2	34	PA13	I/O	FT	JTMS-SWDIO	JTMS-SWDIO	-
C11	73	-	-	-	PH2	I/O	FT	PH2	-	-
F11	74	47	A1	35	V_{SS_2}	S	-	V_{SS_2}	-	-
G11	75	48	B2	36	V_{DD_2}	S	-	V_{DD_2}	-	-
A10	76	49	C3	37	PA14	I/O	FT	JTCK-SWCLK	JTCK-SWCLK	-
A9	77	50	A2	38	PA15	I/O	FT	JTDI	TIM2_CH1_ETR/ SPI1_NSS/ SPI3_NSS/I2S3_WS/ LCD_SEG17/JTDI	-
B11	78	51	B3	-	PC10	I/O	FT	PC10	SPI3_SCK/I2S3_CK/ USART3_TX/ LCD_SEG28/ LCD_SEG40/ LCD_COM4	-

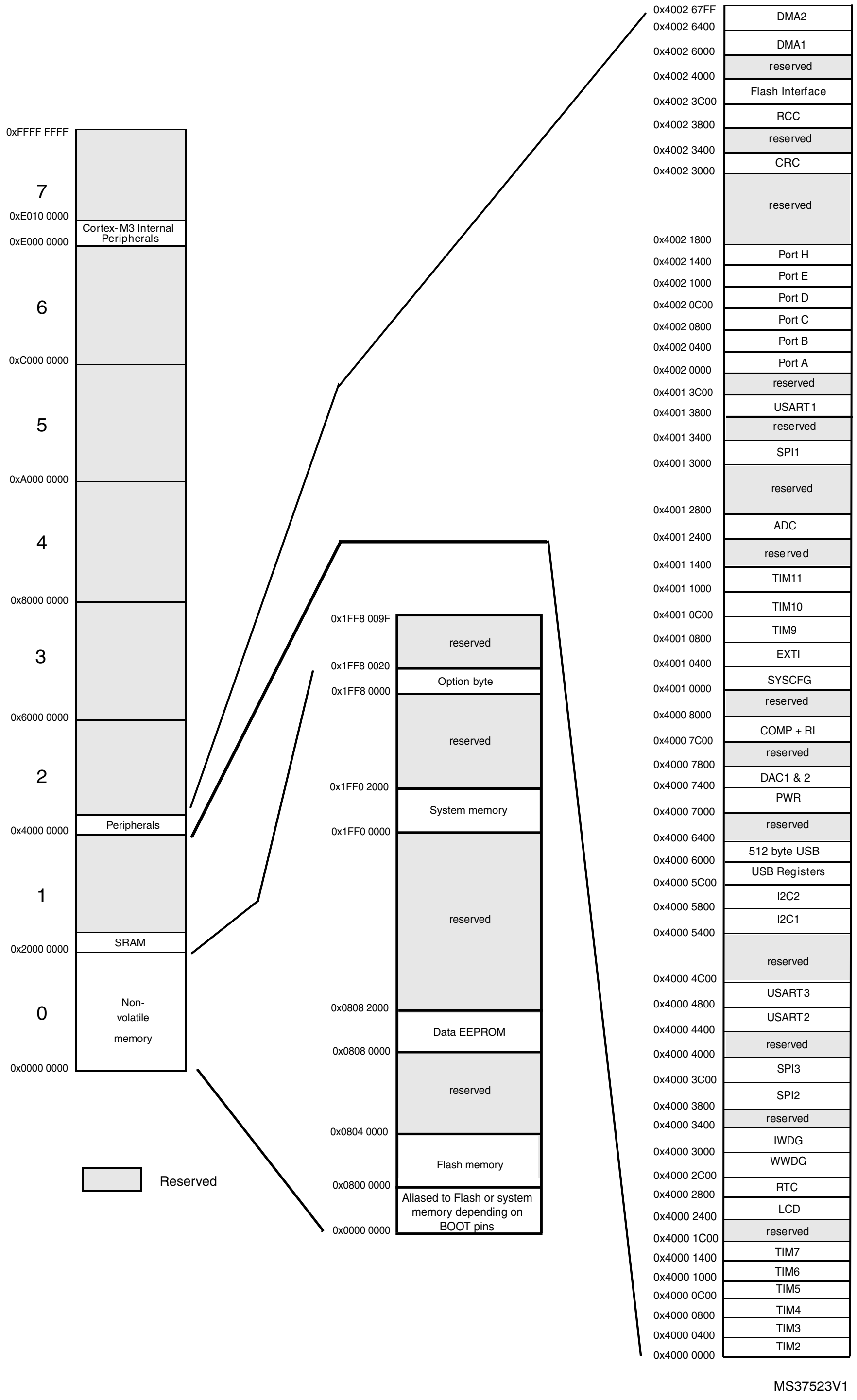
Alternate functions

Table 10. Alternate function input/output

Port name	Digital alternate function number												
	AFIO0	AFIO1	AFIO2	AFIO3	AFIO4	AFIO5	AFIO6	AFIO7	. .	AFIO11	. .	AFIO14	AFIO15
	Alternate function												
	SYSTEM	TIM2	TIM3/4/5	TIM9/ 10/11	I2C1/2	SPI1/2	SPI3	USART1/2/3		LCD		CPRI	SYSTEM
BOOT0	BOOT0	-	-	-	-	-	-	-		-		-	EVENT OUT
NRST	NRST	-	-	-	-	-	-	-		-		-	-
PA0-WKUP1	-	TIM2_CH1_ ETR	TIM5_CH1	-	-	-	-	USART2_CTS		-		TIMx_IC1	EVENT OUT
PA1	-	TIM2_CH2	TIM5_CH2	-	-	-	-	USART2_RTS		SEG0		TIMx_IC2	EVENT OUT
PA2	-	TIM2_CH3	TIM5_CH3	TIM9_CH1	-	-	-	USART2_TX		SEG1		TIMx_IC3	EVENT OUT
PA3	-	TIM2_CH4	TIM5_CH4	TIM9_CH2	-	-	-	USART2_RX		SEG2		TIMx_IC4	EVENT OUT
PA4	-	-	-	-	-	SPI1_NSS	SPI3_NSS I2S3_WS	USART2_CK		-		TIMx_IC1	EVENT OUT
PA5	-	TIM2_CH1_ETR	-	-	-	SPI1_SCK	-	-		-		TIMx_IC2	EVENT OUT
PA6	-	-	TIM3_CH1	TIM10_ CH1	-	SPI1_MISO	-	-		SEG3		TIMx_IC3	EVENT OUT
PA7	-	-	TIM3_CH2	TIM11_ CH1	-	SPI1_MOSI	-	-		SEG4		TIMx_IC4	EVENT OUT
PA8	MCO	-	-	-	-	-	-	USART1_CK		COM0		TIMx_IC1	EVENT OUT
PA9	-	-	-	-	-	-	-	USART1_TX		COM1		TIMx_IC2	EVENT OUT
PA10	-	-	-	-	-	-	-	USART1_RX		COM2		TIMx_IC3	EVENT OUT
PA11	-	-	-	-	-	SPI1_MISO	-	USART1_CTS		-		TIMx_IC4	EVENT OUT
PA12	-	-	-	-	-	SPI1_MOSI	-	USART1_RTS		-		TIMx_IC1	EVENT OUT
PA13	JTMS-SWDIO	-	-	-	-	-	-	-		-		TIMx_IC2	EVENT OUT
PA14	JTCK-SWCLK	-	-	-	-	-	-	-		-		TIMx_IC3	EVEN TOUT
PA15	JTDI	TIM2_CH1_ETR	-	-	-	SPI1_NSS	SPI3_NSS I2S3_WS	-		SEG17		TIMx_IC4	EVEN TOUT

5 Memory mapping

Figure 9. Memory map



6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 11: Voltage characteristics*, *Table 12: Current characteristics*, and *Table 13: Thermal characteristics* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 11. Voltage characteristics

Symbol	Ratings	Min	Max	Unit
$V_{DD}–V_{SS}$	External main supply voltage (including V_{DDA} and V_{DD})(1)	–0.3	4.0	V
V_{IN}(2)	Input voltage on five-volt tolerant pin	V_{SS} –0.3	V_{DD}+4.0	
	Input voltage on any other pin	V_{SS} –0.3	4.0	
$\|\Delta V_{DDx}\|$	Variations between different V_{DD} power pins	-	50	mV
$\|V_{SSX} – V_{SS}\|$	Variations between all different ground pins(3)	-	50	
$V_{REF+} – V_{DDA}$	Allowed voltage difference for $V_{REF+} > V_{DDA}$	-	0.4	V
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	see *Section 6.3.11*		

1. All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. V_{IN} maximum must always be respected. Refer to *Table 12* for maximum allowed injected current values.
3. Include V_{REF-} pin.

Table 12. Current characteristics

Symbol	Ratings	Max.	Unit
$I_{VDD(\Sigma)}$	Total current into sum of all V_{DD_x} power lines (source)(1)	100	mA
$I_{VSS(\Sigma)}$(2)	Total current out of sum of all V_{SS_x} ground lines (sink)(1)	100	
$I_{VDD(PIN)}$	Maximum current into each V_{DD_x} power pin (source)(1)	70	
$I_{VSS(PIN)}$	Maximum current out of each VSS_x ground pin (sink)(1)	-70	
I_{IO}	Output current sunk by any I/O and control pin	25	
	Output current sourced by any I/O and control pin	- 25	
$\Sigma I_{IO(PIN)}$	Total output current sunk by sum of all IOs and control pins(2)	60	
	Total output current sourced by sum of all IOs and control pins(2)	-60	
$I_{INJ(PIN)}$ (3)	Injected current on five-volt tolerant I/O(4), RST and B pins	-5/+0	
	Injected current on any other pin (5)	± 5	
$\Sigma I_{INJ(PIN)}$	Total injected current (sum of all I/O and control pins)(6)	± 25	

1. All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. This current consumption must be correctly distributed over all I/Os and control pins. The total output current must not be sunk/sourced between two consecutive power supply pins referring to high pin count LQFP packages.
3. Negative injection disturbs the analog performance of the device. See note in *Section 6.3.17*.

6.3.3 Embedded internal reference voltage

The parameters given in *Table 17* are based on characterization results, unless otherwise specified.

Table 16. Embedded internal reference voltage calibration values

Calibration value name	Description	Memory address
VREFINT_CAL	Raw data acquired at temperature of 30 °C ±5 °C V_{DDA}= 3 V ±10 mV	0x1FF8 00F8 - 0x1FF8 00F9

Table 17. Embedded internal reference voltage

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{REFINT\ out}$ (1)	Internal reference voltage	– 40 °C < T_J < +110 °C	1.202	1.224	1.242	V
I_{REFINT}	Internal reference current consumption	-	-	1.4	2.3	µA
$T_{VREFINT}$	Internal reference startup time	-	-	2	3	ms
V_{VREF_MEAS}	V_{DDA} and V_{REF+} voltage during V_{REFINT} factory measure	-	2.99	3	3.01	V
A_{VREF_MEAS}	Accuracy of factory-measured V_{REF} value(2)	Including uncertainties due to ADC and V_{DDA}/V_{REF+} values	-	-	±5	mV
T_{Coeff}(3)	Temperature coefficient	–40 °C < T_J < +110 °C	-	25	100	ppm/°C
A_{Coeff}(3)	Long-term stability	1000 hours, T= 25 °C	-	-	1000	ppm
$V_{DDCoeff}$(3)	Voltage coefficient	3.0 V < V_{DDA} < 3.6 V	-	-	2000	ppm/V
$T_{S\_vrefint}$(3)	ADC sampling time when reading the internal reference voltage	-	4	-	-	µs
T_{ADC_BUF}(3) (4)	Startup time of reference voltage buffer for ADC	-	-	-	10	µs
I_{BUF_ADC}(3)	Consumption of reference voltage buffer for ADC	-	-	13.5	25	µA
I_{VREF_OUT}(3)	VREF_OUT output current (5)	-	-	-	1	µA
C_{VREF_OUT}(3)	VREF_OUT output load	-	-	-	50	pF
I_{LPBUF}(3)	Consumption of reference voltage buffer for VREF_OUT and COMP	-	-	730	1200	nA
V_{REFINT_DIV1}(3)	1/4 reference voltage	-	24	25	26	% V_{REFINT}
V_{REFINT_DIV2}(3)	1/2 reference voltage	-	49	50	51	
V_{REFINT_DIV3}(3)	3/4 reference voltage	-	74	75	76	

1. Guaranteed by test in production.
2. The internal V_{REF} value is individually measured in production and stored in dedicated EEPROM bytes.
3. Guaranteed by characterization results.
4. Shortest sampling time can be determined in the application by multiple iterations.

Low-speed external user clock generated from an external source

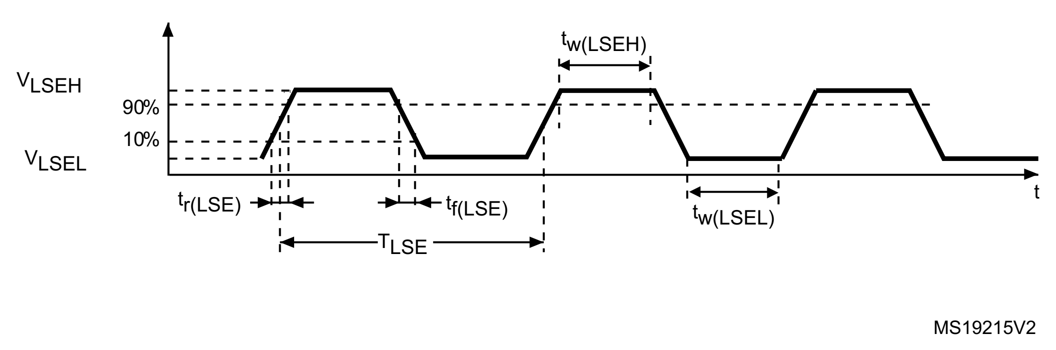
The characteristics given in the following table result from tests performed using a low-speed external clock source, and under the conditions summarized in *Table 14*.

Table 28. Low-speed external user clock characteristics[(1)]

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{LSE_ext}	User external clock source frequency	-	1	32.768	1000	kHz
V_{LSEH}	OSC32_IN input pin high level voltage		$0.7V_{DD}$	-	V_{DD}	V
V_{LSEL}	OSC32_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(LSEH)}$ $t_{w(LSEL)}$	OSC32_IN high or low time		465	-	-	ns
$t_{r(LSE)}$ $t_{f(LSE)}$	OSC32_IN rise or fall time		-	-	10	
$C_{IN(LSE)}$	OSC32_IN input capacitance	-	-	0.6	-	pF

1. Guaranteed by design.

Figure 16. Low-speed external clock source AC timing diagram



High-speed external clock generated from a crystal/ceramic resonator

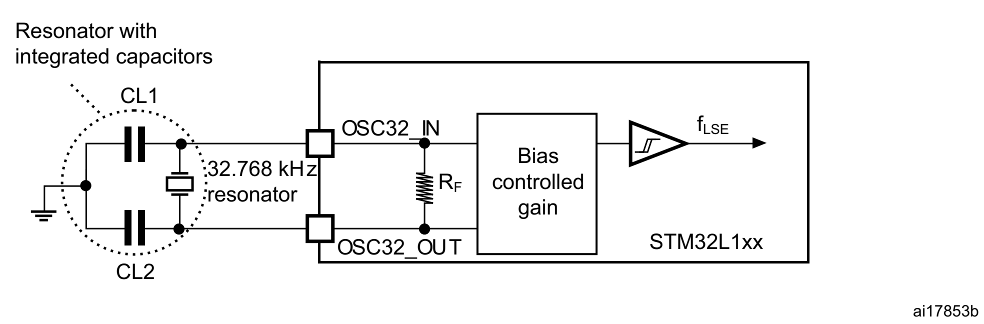
The high-speed external (HSE) clock can be supplied with a 1 to 24 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 29*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

4. $t_{SU(LSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

Note: *For C_{L1} and C_{L2}, it is recommended to use high-quality ceramic capacitors in the 5 pF to 15 pF range selected to match the requirements of the crystal or resonator (see Figure 18). C_{L1} and $C_{L2,}$ are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2}. Load capacitance C_L has the following formula: $C_L = C_{L1} \times C_{L2} / (C_{L1} + C_{L2}) + C_{stray}$ where C_{stray} is the pin capacitance and board or trace PCB-related capacitance. Typically, it is between 2 pF and 7 pF.*

Caution: To avoid exceeding the maximum value of C_{L1} and C_{L2} (15 pF) it is strongly recommended to use a resonator with a load capacitance $C_L \leq 7$ pF. Never use a resonator with a load capacitance of 12.5 pF.
Example: if the user chooses a resonator with a load capacitance of C_L = 6 pF and C_{stray} = 2 pF, then $C_{L1} = C_{L2}$ = 8 pF.

Figure 18. Typical application with a 32.768 kHz crystal



6.3.13 I/O port characteristics

General input/output characteristics

Unless otherwise specified, the parameters given in *Table 49* are derived from tests performed under the conditions summarized in *Table 14*. All I/Os are CMOS and TTL compliant.

Table 43. I/O static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}	Input low level voltage	TC and FT I/O	-	-	0.3 V_{DD}(1)(2)	V
		BOOT0	-	-	0.14 V_{DD}(2)	
V_{IH}	Input high level voltage	TC I/O	0.45 V_{DD}+0.38(2)	-	-	
		FT I/O	0.39 V_{DD}+0.59(2)	-	-	
		BOOT0	0.15 V_{DD}+0.56(2)	-	-	
V_{hys}	I/O Schmitt trigger voltage hysteresis(2)	TC and FT I/O	-	10% V_{DD}(3)	-	
		BOOT0	-	0.01	-	
I_{lkg}	Input leakage current (4)	$V_{SS} \leq V_{IN} \leq V_{DD}$ I/Os with LCD	-	-	±50	nA
		$V_{SS} \leq V_{IN} \leq V_{DD}$ I/Os with analog switches	-	-	±50	
		$V_{SS} \leq V_{IN} \leq V_{DD}$ I/Os with analog switches and LCD	-	-	±50	
		$V_{SS} \leq V_{IN} \leq V_{DD}$ I/Os with USB	-	-	±250	
		$V_{SS} \leq V_{IN} \leq V_{DD}$ TC and FT I/Os	-	-	±50	
		FT I/O $V_{DD} \leq V_{IN} \leq 5V$	-	-	±10	µA
R_{PU}	Weak pull-up equivalent resistor(5)(1)	$V_{IN} = V_{SS}$	30	45	60	kΩ
R_{PD}	Weak pull-down equivalent resistor(5)	$V_{IN} = V_{DD}$	30	45	60	kΩ
C_{IO}	I/O pin capacitance	-	-	5	-	pF

1. Guaranteed by test in production
2. Guaranteed by design.
3. With a minimum of 200 mV.
4. The max. value may be exceeded if negative current is injected on adjacent pins.
5. Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS/NMOS. This MOS/NMOS contribution to the series resistance is minimum (~10% order).

Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to ±8 mA, and sink or source up to ±20 mA with the non-standard V_{OL}/V_{OH} specifications given in *Table 44*.

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in *Section 6.2*:

- The sum of the currents sourced by all the I/Os on $V_{DD,}$ plus the maximum Run consumption of the MCU sourced on $V_{DD,}$ cannot exceed the absolute maximum rating $I_{VDD(\Sigma)}$ (see *Table 12*).
- The sum of the currents sunk by all the I/Os on V_{SS} plus the maximum Run consumption of the MCU sunk on V_{SS} cannot exceed the absolute maximum rating $I_{VSS(\Sigma)}$ (see *Table 12*).

Output voltage levels

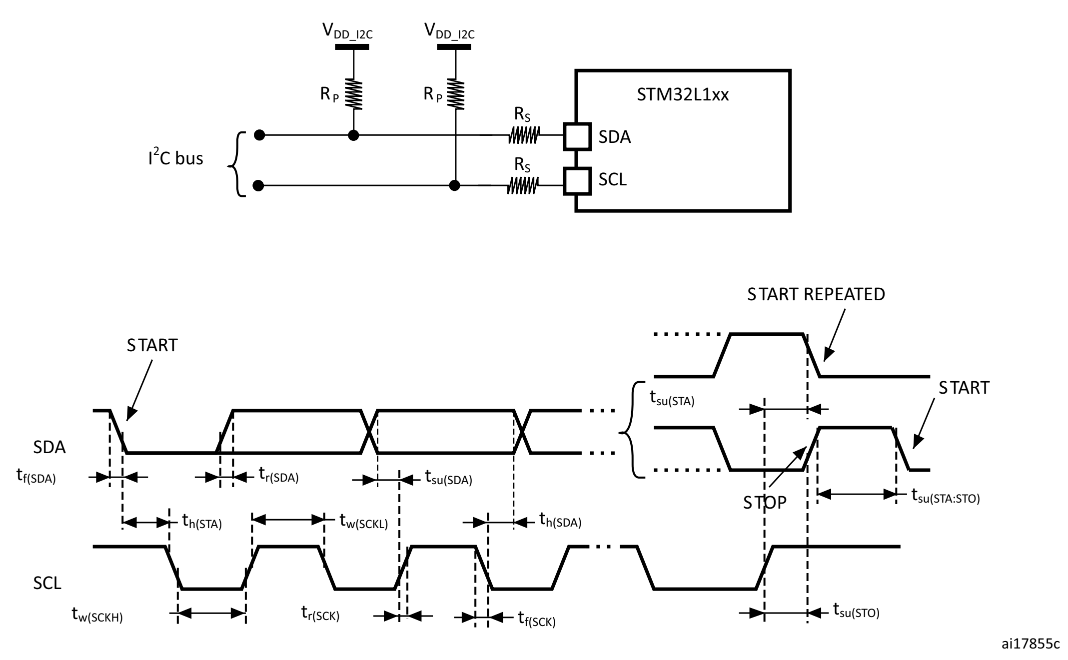
Unless otherwise specified, the parameters given in *Table 44* are derived from tests performed under the conditions summarized in *Table 14*. All I/Os are CMOS and TTL compliant.

Table 44. Output voltage characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
V_{OL} (1)(2)	Output low level voltage for an I/O pin	I_{IO} = 8 mA 2.7 V < V_{DD} < 3.6 V	-	0.4	V
V_{OH}(2)(3)	Output high level voltage for an I/O pin		V_{DD}-0.4	-	
V_{OL} (3)(4)	Output low level voltage for an I/O pin	I_{IO} = 4 mA 1.65 V < V_{DD} < 3.6 V	-	0.45	
V_{OH} (3)(4)	Output high level voltage for an I/O pin		V_{DD}-0.45	-	
V_{OL} (1)(4)	Output low level voltage for an I/O pin	I_{IO} = 20 mA 2.7 V < V_{DD} < 3.6 V	-	1.3	
V_{OH}(3)(4)	Output high level voltage for an I/O pin		V_{DD}-1.3	-	

1. The I_{IO} current sunk by the device must always respect the absolute maximum rating specified in *Table 12* and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VSS}.
2. Guaranteed by test in production.
3. The I_{IO} current sourced by the device must always respect the absolute maximum rating specified in *Table 12* and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VDD}.
4. Guaranteed by characterization results.

Figure 21. I^2C bus AC waveforms and measurement circuit



1. R_S = series protection resistor.
2. R_P = external pull-up resistor.
3. V_{DD_I2C} is the I2C bus power supply.
4. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

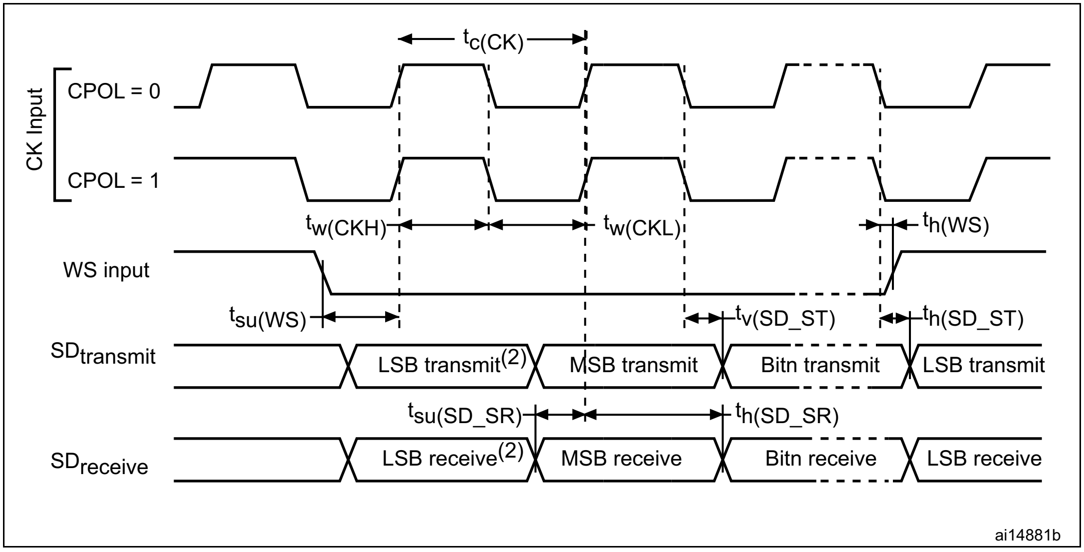
Table 49. SCL frequency (f_{PCLK1}= 32 MHz, V_{DD} = V_{DD_I2C} = 3.3 V)(1)(2)

f_{SCL} (kHz)	I2C_CCR value
	R_P = 4.7 kΩ
400	0x801B
300	0x8024
200	0x8035
100	0x00A0
50	0x0140
20	0x0320

1. R_P = External pull-up resistance, f_{SCL} = I^2C speed.
2. For speeds around 200 kHz, the tolerance on the achieved speed is of ±5%. For other speed ranges, the tolerance on the achieved speed is ±2%. These variations depend on the accuracy of the external components used to design the application.

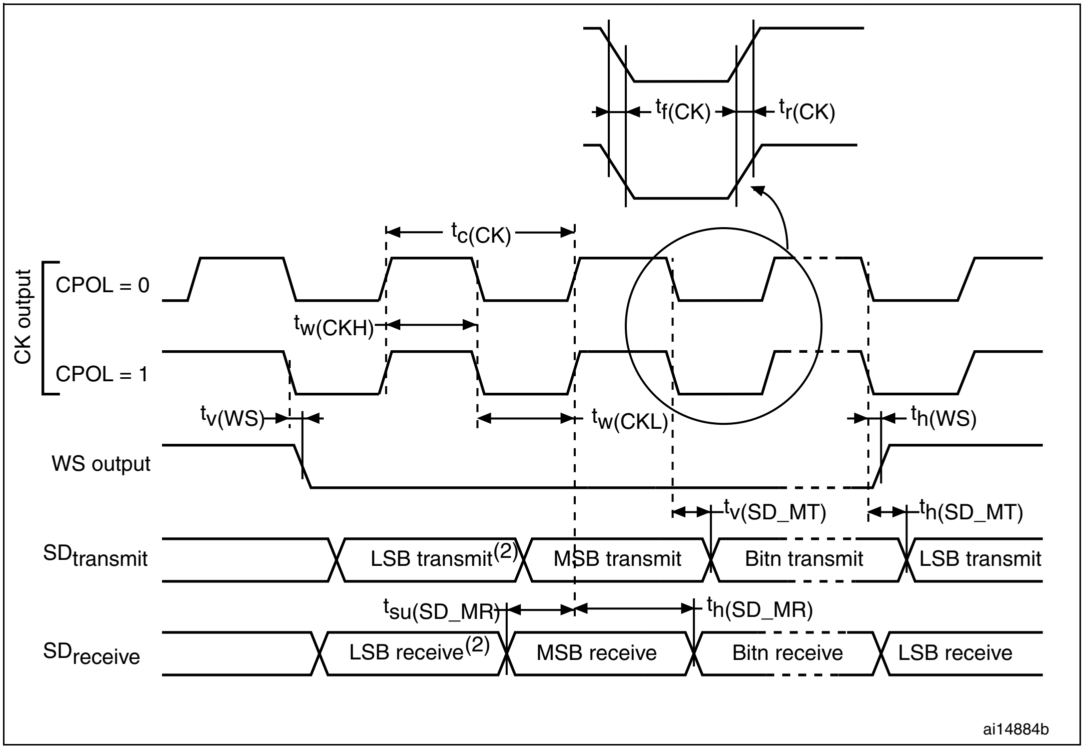
*ODD bit value, digital contribution leads to a min of (I2SDIV/(2*I2SDIV+ODD) and a max of (I2SDIV+ODD)/(2*I2SDIV+ODD). Fs max is supported for each mode/condition.*

Figure 26. I^2S slave timing diagram (Philips protocol)(1)



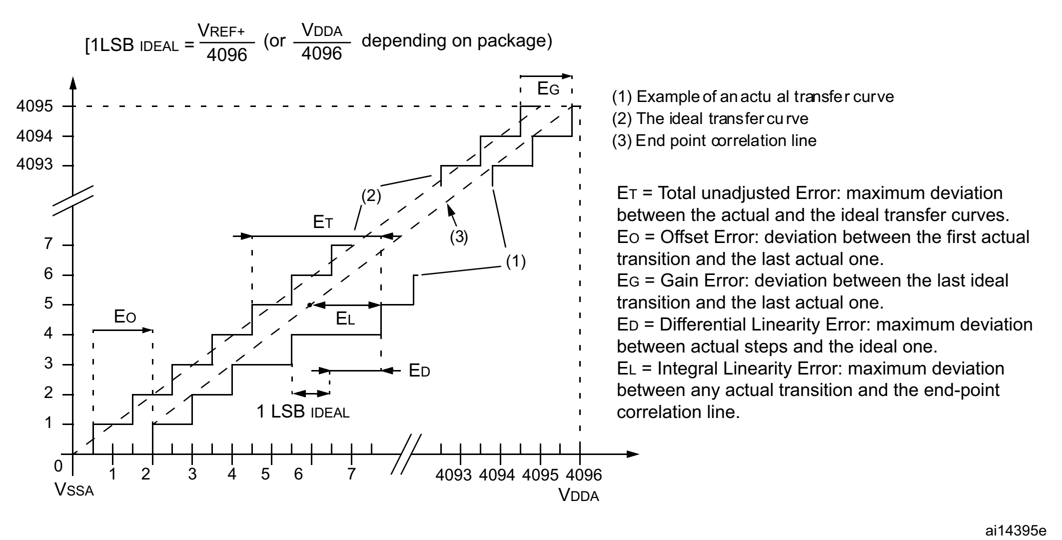
1. Measurement points are done at CMOS levels: 0.3 × V_{DD} and 0.7 × V_{DD}.
2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

Figure 27. I^2S master timing diagram (Philips protocol)(1)



1. Guaranteed by characterization results.
2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

Figure 28. ADC accuracy characteristics



ET = Total unadjusted Error: maximum deviation between the actual and the ideal transfer curves.

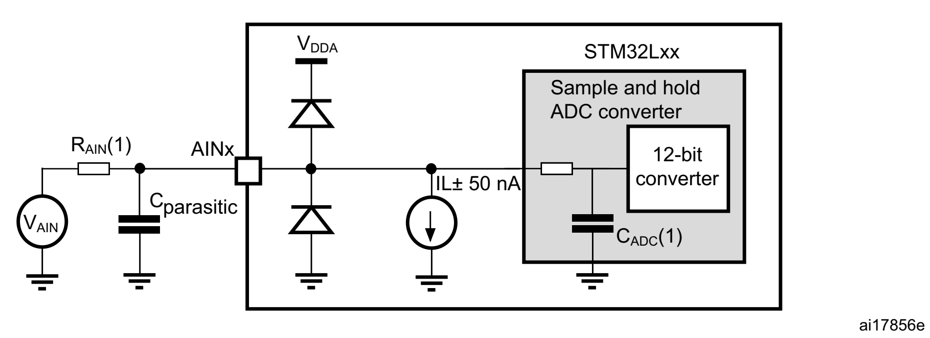
EO = Offset Error: deviation between the first actual transition and the last actual one.

EG = Gain Error: deviation between the last ideal transition and the last actual one.

ED = Differential Linearity Error: maximum deviation between actual steps and the ideal one.

EL = Integral Linearity Error: maximum deviation between any actual transition and the end-point correlation line.

Figure 29. Typical connection diagram using the ADC



1. Refer to *Table 58: Maximum source impedance RAIN max* for the value of R_{AIN} and *Table 56: ADC characteristics* for the value of C_{ADC}.
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high $C_{parasitic}$ value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.

6.3.20 Temperature sensor characteristics

Table 61. Temperature sensor calibration values

Calibration value name	Description	Memory address
TS_CAL1	TS ADC raw data acquired at temperature of 30 °C ±5 °C V_{DDA}= 3 V ±10 mV	0x1FF8 00FA - 0x1FF8 00FB
TS_CAL2	TS ADC raw data acquired at temperature of 110 °C ±5 °C V_{DDA}= 3 V ±10 mV	0x1FF8 00FE - 0x1FF8 00FF

Table 62. Temperature sensor characteristics

Symbol	Parameter	Min	Typ	Max	Unit
T_L(1)	V_{SENSE} linearity with temperature	-	±1	±2	°C
Avg_Slope(1)	Average slope	1.48	1.61	1.75	mV/°C
V_{110}	Voltage at 110°C ±5°C(2)	612	626.8	641.5	mV
$I_{DDA(TEMP)}$(3)	Current consumption	-	3.4	6	µA
t_{START}(3)	Startup time	-	-	10	µs
T_{S_temp}(3)	ADC sampling time when reading the temperature	4	-	-	

1. Guaranteed by characterization results.
2. Measured at V_{DD} = 3 V ±10 mV. V110 ADC conversion result is stored in the TS_CAL2 byte.
3. Guaranteed by design.

6.3.21 Comparator

Table 63. Comparator 1 characteristics

Symbol	Parameter	Conditions	Min(1)	Typ	Max(1)	Unit
V_{DDA}	Analog supply voltage	-	1.65		3.6	V
R_{400K}	R_{400K} value	-	-	400	-	kΩ
R_{10K}	R_{10K} value	-	-	10	-	
V_{IN}	Comparator 1 input voltage range	-	0.6	-	V_{DDA}	V
t_{START}	Comparator startup time	-	-	7	10	µs
td	Propagation delay(2)	-	-	3	10	
Voffset	Comparator offset	-	-	±3	±10	mV
$d_{Voffset}/dt$	Comparator offset variation in worst voltage stress conditions	V_{DDA} = 3.6 V V_{IN+} = 0 V V_{IN-} = V_{REFINT} T_A = 25 °C	0	1.5	10	mV/1000 h
I_{COMP1}	Current consumption(3)	-	-	160	260	nA

Table 75. Document revision history (continued)

Date	Revision	Changes
09-Dec-2013	6	Apply footnote 1 also to VDD= 1.8 to 2.0 V in *Table 2: Functionalities depending on the operating power supply range*. Updated I_{inj} pin in *Table 11: Current characteristics*. Added Input Voltage in *Table 13: General operating conditions*. Updated Input leakage current conditions in *Table 63: I/O static characteristics* Removed minimum value for $f_S$in *Table 77: ADC characteristics*. Removed Fi_{nput} for ENOB,SINAD,SNR,THD in *Table 78: ADC accuracy*. Added tolerance for TS_CAL1 and TS_CAL2 in *Table 82: Temperature sensor calibration values*.
13-Mar-2014	7	Updated *Section 3.7: Memories*, *Table 33: Peripheral current consumption* : updated Flash value, *Table 61: I/O current injection susceptibility*, *Table 63: I/O static characteristics*:added BOOT0 pin *Table 66: NRST pin characteristics*, *Chapter 2.2: Ultra-low-power device continuum*. removed figures “Power supply and reference decoupling (V_{REF+} not connected to V_{DDA}) and “Power supply and reference decoupling(V_{REF+} connected to V_{DDA}). Updated *Table 19: Current consumption in Run mode, code with data processing running from Flash* Updated *Section 6.3.1: General operating conditions*. Updated *Table 80: DAC characteristics* Added marking for LQFP48/UFQFPN48 packages Updated *Table 66: NRST pin characteristics* Updated *Table 63: I/O static characteristics*
16-May-2014	8	Updated I_{IO} in *Table 12: Current characteristics*. Updated conditions in *Table 44: Output voltage characteristics*. Removed note 4 in *Table 62: Temperature sensor characteristics* Updated the conditions in *Table 26: Low-power mode wakeup timings*. Removed ambiguity of “ambient temperature” in the electrical characteristics description.
13-Oct-2014	9	Updated *Section 3.17: Communication interfaces* putting I2S characteristics inside. Updated DMIPS features in cover page and *Section 2: Description*. Updated max temperature at 105°C instead of 85°C in the whole datasheet. Updated current consumption in *Table 20: Current consumption in Sleep mode*. Updated *Table 25: Peripheral current consumption* with new measured current values. Updated *Table 58: Maximum source impedance RAIN max* adding note 2.
06-Mar-2015	10	Updated *Section 7: Package information* with new package device marking. Updated *Figure 9: Memory map*.